Silicon PNP Power Transistors 2SB337

DESCRIPTION

·With TO-3 package

·Low collector saturation voltage

APPLICATIONS

·For audio frequency power output applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-40	V
V_{CEO}	Collector-emitter voltage	Open base	-30	V
V_{EBO}	Emitter-base voltage	Open collector	-10	V
I_C	Collector current		-7	A
I_E	Emitter current		7	A
I_B	Base current		-1	A
P_C	Collector power dissipation	$T_C \le 55$□	30	W
T_j	Junction temperature		100	□
T_{stg}	Storage temperature		-55~100	□

CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-10mA; I_B=0	-30			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-1mA; I_C=0	-10			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-4A; I_B=-0.4A		-0.29		V
V_{BE}	Base-emittter on voltage	I_C=-1A ;V_{CE}=-2V		-0.38		V
I_{CBO}	Collector cut-off current	V_{CB}=-30V; I_E=0			-0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=-10V; I_E=0			-0.1	mA
h_{FE}	DC current gain	I_C=-1A ; V_{CE}=-2V	50	90	165	

◆ h_{FE} Classifications

A	B
50-100	80-165

PACKAGE OUTLINE

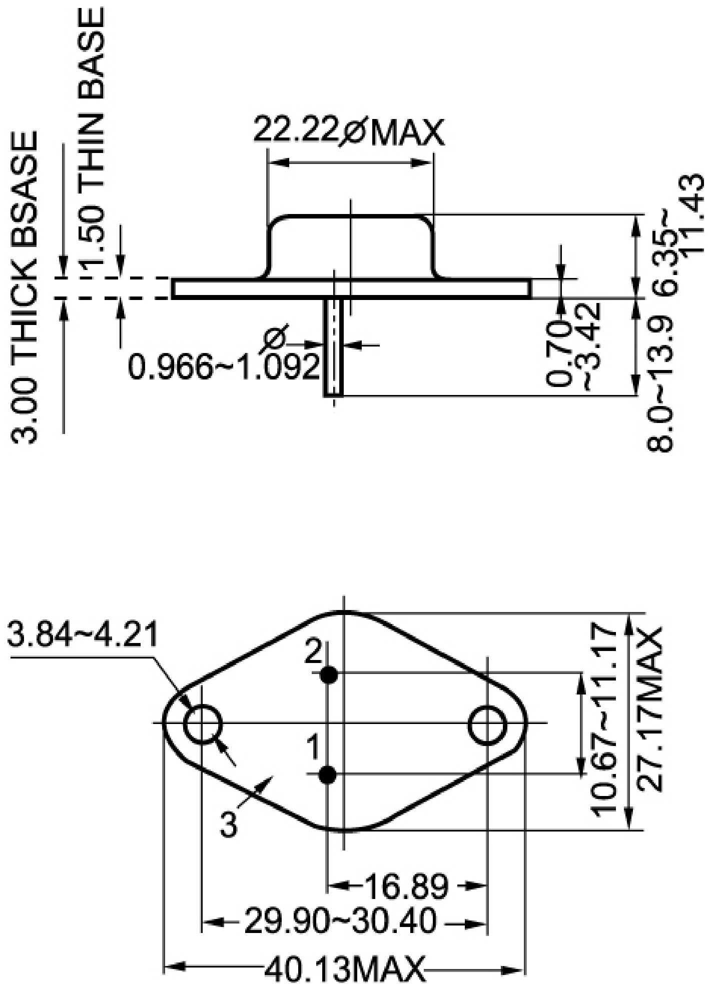

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)